

**Silicon PNP Power Transistors**

**2SB979**

**DESCRIPTION**

With TO-3PN package  
 ·Wide area of safe operation

**APPLICATIONS**

·For power amplifier and general purpose applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

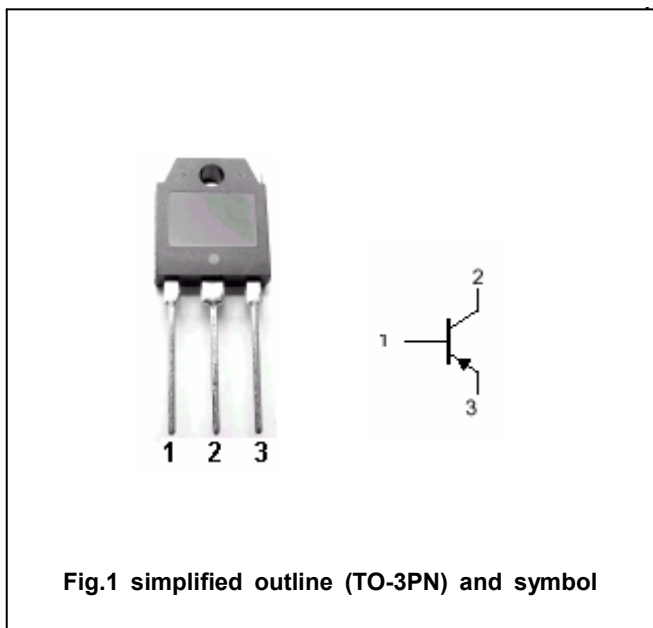


Fig.1 simplified outline (TO-3PN) and symbol

**Absolute maximum ratings(Tc=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-100	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	60	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-30mA ; I_B=0$	-100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-5mA ; I_E=0$	-100			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-5mA ; I_C=0$	-5			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=-3A ; I_B=-0.3A$			-1.5	V
$V_{BE}$	Base-emitter on voltage	$I_C=-1A ; V_{CE}=-5V$			-1.5	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=-100V ; I_E=0$			-50	$\mu A$
$I_{EBO}$	Emitter cut-off current	$V_{EB}=-5V ; I_C=0$			-50	$\mu A$
$h_{FE-1}$	DC current gain	$I_C=-1A ; V_{CE}=-5V$	40		200	
$h_{FE-2}$	DC current gain	$I_C=-3A ; V_{CE}=-5V$	20			
$f_T$	Transition frequency	$I_C=-1A ; V_{CE}=-5V$	20			MHz

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PACKAGE OUTLINE

